5.0 V ECL 2:1 Multiplexer

Description

The MC10EL/100EL58 is a 2:1 multiplexer. The device is functionally equivalent to the E158 device with higher performance capabilities. With propagation delays and output transition times significantly faster than the E158, the EL58 is ideally suited for those applications which require the ultimate in AC performance.

The 100 Series contains temperature compensation.

Features

- 230 ps Propagation Delay
- PECL Mode Operating Range:
 - $V_{CC} = 4.2 \text{ V}$ to 5.7 V with $V_{EE} = 0 \text{ V}$
- NECL Mode Operating Range:
 - $V_{CC} = 0$ V with $V_{EE} = -4.2$ V to -5.7 V
- Internal Input Pulldown Resistors on D_a, D_b, and SEL
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

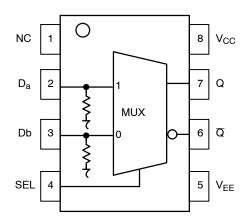


Figure 1. Logic Diagram and Pin Assignment

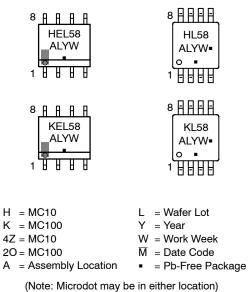






SOIC-8 NB D SUFFIX CASE 751-07

TSSOP-8 DT SUFFIX CASE 948R-02



MARKING DIAGRAMS*

*For additional marking information, refer to

Application Note <u>AND8002/D</u>.

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

Table 1. PIN DESCRIPTION

PIN	FUNCTION							
D _a , Db	ECL Data Inputs							
Q, <u>Q</u>	ECL Data Outputs							
SEL	ECL Select Input							
V _{CC}	Positive Supply							
V_{EE}	Negative Supply							
NC	No Connect							

Table 2. FUNCTION TABLE

SEL*	Data
ΤL	a b

* Pin will default low when left open.

Table 3. ATTRIBUTES

Characteristics	Value						
Internal Input Pulldown Resistor	75 kΩ						
Internal Input Pullup Resistor	N/A						
ESD Protection Human Body Model Machine Model	> 1 kV > 100 V						
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1) SOIC-8 TSSOP-8	Level 1 Level 3						
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in						
Transistor Count	45						
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test							

1. Refer to Application Note <u>AND8003/D</u> for additional information.

Table 4. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		8	V
V_{EE}	NECL Mode Power Supply	V _{CC} = 0 V		-8	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$\begin{array}{l} V_I \leq V_{CC} \\ V_I \geq V_{EE} \end{array}$	6 -6	V
l _{out}	Output Current	Continuous Surge		50 100	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)		SOIC-8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
T _{sol}	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

Table 5. 10EL SERIES PECL DC CHARACTERISTICS (V_{CC} = 5.0 V; V_{EE} = 0.0 V (Note 1))

		-40°C			25°C						
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current		14	17		14	17		14	17	mA
V _{OH}	Output HIGH Voltage (Note 2)	3920	4010	4110	4020	4105	4190	4090	4185	4280	mV
V _{OL}	Output LOW Voltage (Note 2)	3050	3200	3350	3050	3210	3370	3050	3227	3405	mV
V _{IH}	Input HIGH Voltage	3770		4110	3870		4190	3940		4280	mV
V _{IL}	Input LOW Voltage	3050		3500	3050		3520	3050		3555	mV
I _{IH}	Input HIGH Current			150			150			150	μA
۱ _{IL}	Input LOW Current	0.5			0.5			0.3			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.06 V / –0.5 V.

2. Outputs are terminated through a 50 ohm resistor to $V_{CC}\mathchar`-2$ volts.

		-40°C				25°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current		14	17		14	17		14	17	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1080	-990	-890	-980	-895	-810	-910	-815	-720	mV
V _{OL}	Output LOW Voltage (Note 2)	-1950	-1800	-1650	-1950	-1790	-1630	-1950	-1773	-1595	mV
VIH	Input HIGH Voltage	-1230		-890	-1130		-810	-1060		-720	mV
V_{IL}	Input LOW Voltage	-1950		-1500	-1950		-1480	-1950		-1445	mV
I _{IH}	Input HIGH Current			150			150			150	μA
۱ _{IL}	Input LOW Current	0.5			0.5			0.3			μA

Table 6. 10EL SERIES NECL DC CHARACTERISTICS (V_{CC}= 0.0 V; V_{EE}= -5.0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.06 V / –0.5 V.

2. Outputs are terminated through a 50 ohm resistor to V_{CC} -2 volts.

		-40°C			25°C						
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current		14	17		14	17		16	19	mA
V _{OH}	Output HIGH Voltage (Note 2)	3915	3995	4120	3975	4045	4120	3975	4050	4120	mV
V _{OL}	Output LOW Voltage (Note 2)	3170	3305	3445	3190	3295	3380	3190	3295	3380	mV
V _{IH}	Input HIGH Voltage	3835		4120	3835		4120	3835		4120	mV
V _{IL}	Input LOW Voltage	3190		3525	3190		3525	3190		3525	mV
I _{IH}	Input HIGH Current			150			150			150	μA
Ι _{ΙL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.8 V / –0.5 V.

2. Outputs are terminated through a 50 ohm resistor to V_{CC} -2 volts.

			−40°C			25°C			85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	
I _{EE}	Power Supply Current		14	17		14	17		16	19	mA	
V _{OH}	Output HIGH Voltage (Note 2)	-1085	-1005	-880	-1025	-955	-880	-1025	-955	-880	mV	
V _{OL}	Output LOW Voltage (Note 2)	-1830	-1695	-1555	-1810	-1705	-1620	-1810	-1705	-1620	mV	
VIH	Input HIGH Voltage	-1165		-880	-1165		-880	-1165		-880	mV	
V _{IL}	Input LOW Voltage	-1810		-1475	-1810		-1475	-1810		-1475	mV	
I _{IH}	Input HIGH Current			150			150			150	μΑ	
Ι _{ΙL}	Input LOW Current	0.5			0.5			0.5			μA	

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.8 V / –0.5 V.

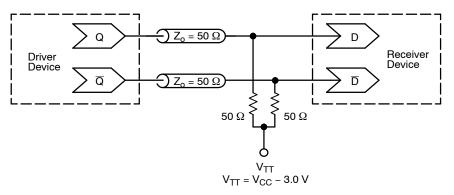
2. Outputs are terminated through a 50 ohm resistor to V_{CC} -2 volts.

		-40°C			25°C						
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
fmax	Maximum Toggle Frequency					1.5					GHz
t _{PLH} t _{PHL}	Propagation Delay to Output D to Q SEL to Q	60 90	220 250	380 410	120 150	230 260	340 370	140 170	250 280	360 390	ps
t _{JITTER}	Random Clock Jitter (RMS)					0.9					ps
t _r t _f	Output Rise/Fall Times Q (20% – 80%)	100	225	350	100	225	350	100	225	350	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. 10 Series: V_{EE} can vary +0.06 V / -0.5 V.

100 Series: V_{EE} can vary +0.8 V / –0.5 V.





ORDERING INFORMATION

Device	Package	Shipping [†]	
MC10EL58DG	SOIC-8 (Pb-Free)	98 Units / Rail	
MC10EL58DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel	
MC10EL58DTG	TSSOP-8 (Pb-Free)	100 Units / Rail	
MC100EL58DG	SOIC-8 (Pb-Free)	98 Units / Rail	
MC100EL58DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel	
MC100EL58DTG	TSSOP-8 (Pb-Free)	100 Units / Rail	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

Resource Reference of Application Notes

AN1405/D	-	ECL Clock Distribution Techniques	
AN1406/D	-	Designing with PECL (ECL at +5.0 V)	
AN1503/D	-	ECLinPS [™] I/O SPiCE Modeling Kit	
AN1504/D	-	Metastability and the ECLinPS Family	
AN1568/D	-	Interfacing Between LVDS and ECL	
AN1672/D	-	The ECL Translator Guide	
AND8001/D	-	Odd Number Counters Design	
AND8002/D	-	Marking and Date Codes	
AND8020/D	-	Termination of ECL Logic Devices	
AND8066/D	-	Interfacing with ECLinPS	
AND8090/D	_	AC Characteristics of ECL Devices	

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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COLLECTOR, #1

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